

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	0	("(si-ge) near25(substrate)").PN.	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
2	IS&R	L2	0	("(si-ge) near25(substrate)").PN.	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
3	BRS	L3	340	(si-ge) near35 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
4	BRS	L4	86	3 and (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	1365	(silicon-germanium) near35 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
6	BRS	L6	11	(silicon-germanium) near5 (epi\$5) near35 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
7	BRS	L7	36	(silicon near germanium) near5 (epi\$5) near35 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
8	BRS	L8	5853	(silicon near germanium) near35 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	1157	8 and (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	15	8 and (epi\$5) near15 (discont\$4 or nucleat\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	2	"5273930".pn.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	3	(si-ge) near (epit\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	31	(si-ge) near10 (epit\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	31	(Si-Ge) near10 (epit\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	5	(ge-si) near10 (epit\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	37	(semiconductor near seed near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	13260	(seed near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	31	(seed near layer) near35 (si-ge or ge-si)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	34	(seed) near35 (si-ge or ge- si)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	1444	(si-ge or ge-si)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	1280	(si-ge)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
22	BRS	L22	213	(ge-si)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
23	BRS	L23	2	(ge-si) near35 (seed)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
24	BRS	L24	32	(si-ge) near15 (seed)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	16231	(si near ge) or (ge near si)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
2	BRS	L2	23	((si near ge) or (ge near si)) near (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
3	BRS	L3	4	((si-ge) or (ge-si)) near (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
4	BRS	L4	41	((silicon-germanium) or (germanium-silicon)) near (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	0	((si-germanium) or (germanium-si)) near (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	62	((silicon near germanium) or (germanium near silicon)) near (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	0	((si near germanium) or (germanium near si)) near (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	0	((si-germanium) or (germanium-si)) near (epi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	299	((si near ge) or (ge near si)) near (crystal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
10	BRS	L10	68	((si-ge) or (ge-si)) near (crystal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
11	BRS	L11	212	((silicon-germanium) or (germanium-silicon)) near (crystal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
12	BRS	L12	909	((silicon near germanium) or (germanium near silicon)) near (crystal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	0	(si-ge) near15 (discont\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
26	BRS	L26	4	(si-ge) and (discont\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
27	BRS	L27	1039	(si-ge) and (cont\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
28	BRS	L28	33	((si-ge) near25 (epi\$5)) and (cont\$5)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	U	1	Document ID	Title
1			US 20030116187 A1	Tandem Si-Ge solar cell with improved conversion efficiency
2			US 6613974 B2	Tandem Si-Ge solar cell with improved conversion efficiency
3			US 6325858 B1	Long life high temperature process chamber